MOSFET – Dual, N-Channel, **Small Signal, SC-88**

30 V, 250 mA

Features

- Low Gate Charge for Fast Switching
- Small Footprint 30% Smaller than TSOP-6
- ESD Protected Gate
- AEC Q101 Qualified NVTJD4001N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Low Side Load Switch
- Li-Ion Battery Supplied Devices Cell Phones, PDAs, DSC
- Buck Converters
- Level Shifts

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage	V_{DSS}	30	V		
Gate-to-Source Voltage	1		V _{GS}	±20	V
Continuous Drain	Steady State	T _A = 25 °C	I _D	250	mA
Current (Note 1)	State	T _A = 85 °C		180	
Power Dissipation (Note 1)	Steady State	T _A = 25 °C	P _D	272	mW
Pulsed Drain Current	I _{DM}	600	mA		
Operating Junction and Storage Temperature			T _J , T _{STG}	–55 to 150	°C
Source Current (Body Diode)			I _S	250	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State	$R_{\theta JA}$	458	°C/W
Junction-to-Lead - Steady State	$R_{ heta JL}$	252	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

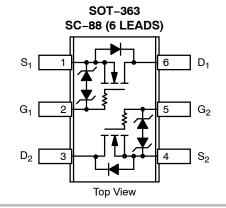
1. Surface mounted on FR4 board using min pad size (Cu area = 0.155 in sq [1 oz] including traces).



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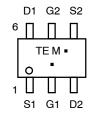
www.onsemi.com

V _{(BR)DSS}	/ _{(BR)DSS} R _{DS(on)} TYP	
20.1/	1.0 Ω @ 4.0 V	250 mA
30 V	1.5 Ω @ 2.5 V	250 IIIA



MARKING DIAGRAM & PIN ASSIGNMENT





ΤE = Device Code М = Date Code = Pb-Free Package

ORDERING INFORMATION

(Note: Microdot may be in either location)

Device	Package	Shipping [†]
NTJD4001NT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NVTJD4001NT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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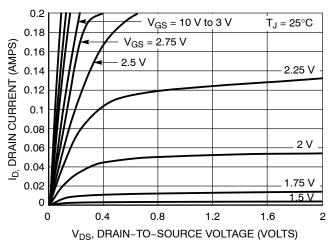
ELECTRICAL CHARACTERISTICS (T_{.I} = 25°C unless otherwise stated)

Parameter	Symbol	Test Con	dition	Min	Тур	Max	Unit
OFF CHARACTERISTICS			<u> </u>				
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V, } I_{D}$) = 100 μΑ	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				56		mV/ °C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V	_{DS} = 30 V			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V ₀	_{GS} = ±10 V			±1.0	μΑ
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_{I}$	ο = 100 μΑ	8.0	1.2	1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J				-3.2		mV/ °C
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 4.0 \text{ V}, I_D = 10 \text{ mA}$ $V_{GS} = 2.5 \text{ V}, I_D = 10 \text{ mA}$			1.0	1.5	Ω
					1.5	2.5	
Forward Transconductance	g _{FS}	V _{DS} = 3.0 V, I _D = 10 mA			80		mS
CHARGES AND CAPACITANCES							
Input Capacitance	C _{ISS}	$V_{GS} = 0 \text{ V, } f = 1.0 \text{ MHz,}$			20	33	pF
Output Capacitance	C _{OSS}	$V_{DS} = 5$	5.0 V		19	32	
Reverse Transfer Capacitance	C _{RSS}				7.25	12	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 5.0 V, V _{DS} = 24 V,			0.9	1.3	nC
Threshold Gate Charge	Q _{G(TH)}	$I_D = 0$.	1 A		0.2		7
Gate-to-Source Charge	Q _{GS}				0.3		
Gate-to-Drain Charge	Q_{GD}				0.2		
SWITCHING CHARACTERISTICS (No	ote 3)						
Turn-On Delay Time	td _(ON)	V _{GS} = 4.5 V, V			17		ns
Rise Time	tr	$I_D = 10 \text{ mA}, I$	HG = 20.75		23		
Turn-Off Delay Time	td _(OFF)				94		
Fall Time	tf				82		
DRAIN-SOURCE DIODE CHARACTE	RISTICS						
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V,	T _J = 25°C		0.65	0.7	V
		$I_S = 10 \text{ mA}$	T _J = 125°C		0.45		
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V, } dI_{S}/c$ $I_{S} = 10$			12.4		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 2. Pulse Test: pulse width \leq 300 $\mu s,$ duty cycle \leq 2%.
- 3. Switching characteristics are independent of operating junction temperatures.

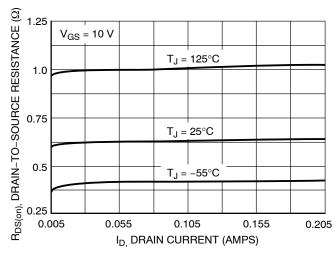
TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)



 $V_{DS} = 5 V$ ID, DRAIN CURRENT (AMPS) 0.08 0.06 $T_J = 125^{\circ}C$ 0.04 0.02 $T_J = -55^{\circ}C$ 0 1.2 1.6 1.4 1.8 2 2.2 1 V_{GS}, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



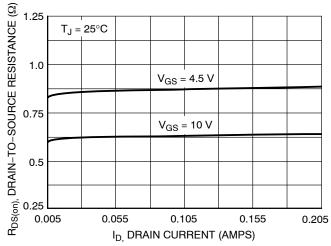
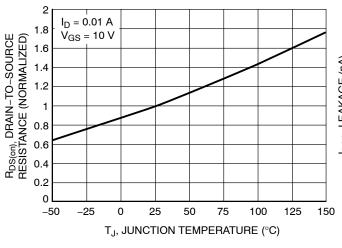


Figure 3. On-Resistance vs. Drain Current and Temperature

Figure 4. On-Resistance vs. Drain Current and Gate Voltage



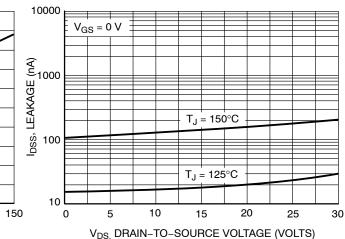
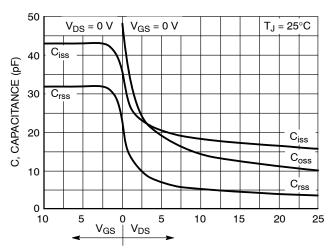
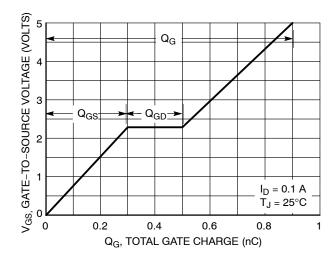


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)





GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. Capacitance Variation

Figure 8. Gate-to-Source Voltage vs. Total Gate Charge

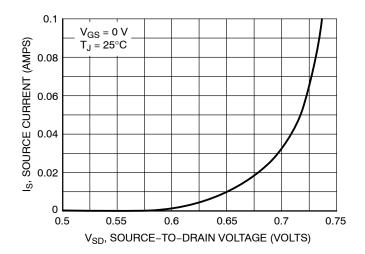


Figure 9. Diode Forward Voltage vs. Current

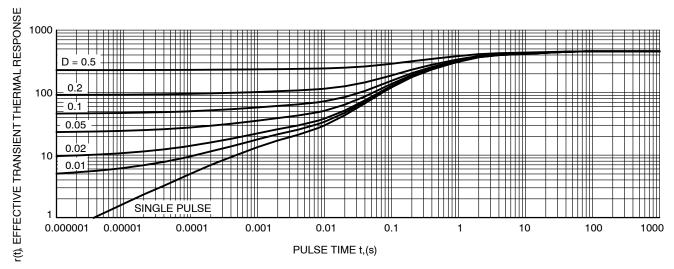


Figure 10. Thermal Response

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DATE 11 DEC 2012





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS
- CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.

- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65 BSC			.026 BS	С
L	0.26	0.36	0.46	0.010	0.014	0.018
L2		0.15 BS	C	0.006 BSC		
aaa		0.15			0.006	
bbb	0.30				0.012	
ccc	0.10				0.004	
ddd		0.10			0.004	

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

- *Date Code orientation and/or position may vary depending upon manufacturing location.
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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